

## MICROWAVE POWER GAAS FET

# TIM4450-60SL

#### MICROWAVE SEMICONDUCTOR TECHNICAL DATA

#### **FEATURES**

- ·BROAD BAND INTERNALLY MATCHED FET
- ·HIGH POWER

P1dB= 48.0dBm at 4.4GHz to 5.0GHz

·HIGH GAIN

G1dB= 9.5dB at 4.4GHz to 5.0GHz

**LOW INTERMODULATION DISTORTION** 

IM3(MIN.) = -42dBc at Pout= 36.5dBm (Single Carrier Level)

·HERMETICALLY SEALED PACKAGE



## RF PERFORMANCE SPECIFICATIONS (Ta=25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain Compression Point	P1dB	VDS= 10V IDSset= 9.5A f= 4.4 to 5.0GHz  Two-Tone Test Po= 36.5dBm, Δf= 5MHz (Single Carrier Level)	dBm	47.0	48.0	_
Power Gain at 1dB Gain Compression Point	G1dB		dB	8.5	9.5	
Drain Current	IDS1		Α	_	13.2	15.0
Gain Flatness	ΔG		dB	_	_	±0.8
Power Added Efficiency	ηadd		%	_	42	_
3rd Order Intermodulation Distortion	IM3		dBc	-42	-45	
Drain Current	IDS2		Α	_		11.8
Channel Temperature Rise	ΔTch	(VDS × IDS + Pin – P1dB) × Rth(c-c)	°C	_		100

Recommended Gate Resistance(Rg): 28 Ω

## **ELECTRICAL CHARACTERISTICS (Ta=25°C)**

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V IDS= 12.0A	S	_	20	_
Pinch-off Voltage	VGSoff	VDS= 3V IDS= 200mA	V	-1.0	-1.8	-3.0
Saturated Drain Current	IDSS	VDS= 3V VGS= 0V	Α	_	38	_
Gate-Source Breakdown Voltage	VGSO	IGS= -1.0mA	V	-5	_	_
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W	_	0.6	0.8

- MICROWAVE SEMICONDUCTOR TECHNICAL DATA

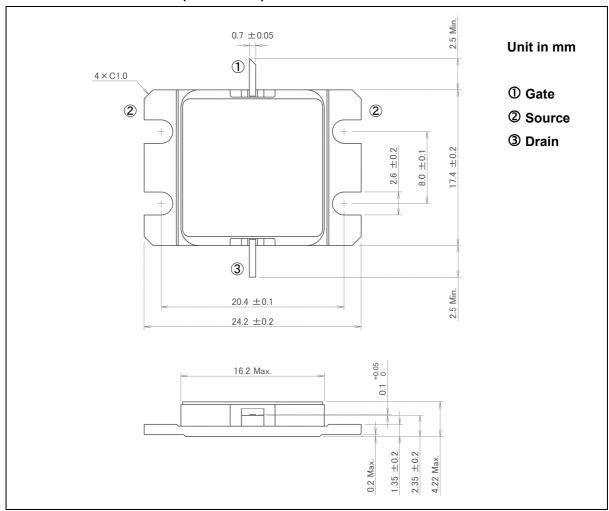
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## ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	15
Gate-Source Voltage	VGS	V	-5
Drain Current	IDS	А	20
Total Power Dissipation (Tc= 25°C)	PT	W	187
Channel Temperature	Tch	°C	175
Storage Temperature	Tstg	°C	-65 to +175

## PACKAGE OUTLINE (2-16G1B)



## HANDLING PRECAUTIONS FOR PACKAGE MODEL

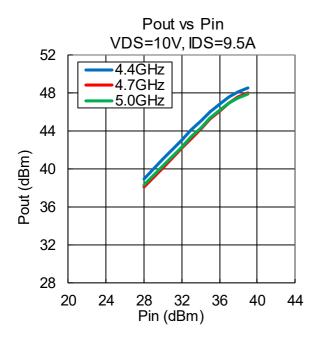
Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds at 350°C.

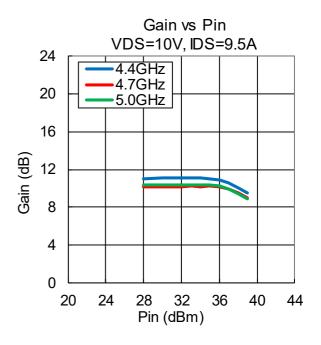


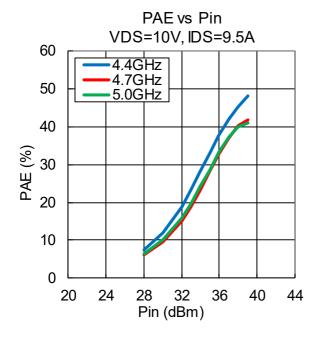
#### TYPICAL RF PERFORMANCE

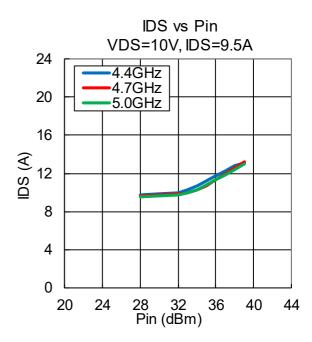
·Pout, Gain, PAE, IDS vs. Pin

VDS= 10 V, IDSset= 9.5 A, f= 4.4, 4.7, 5.0 GHz, Ta= +25 °C



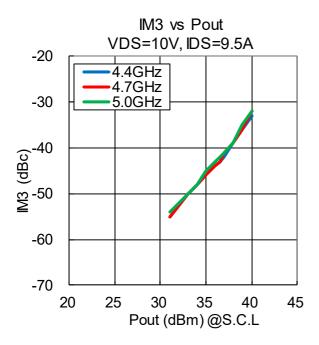






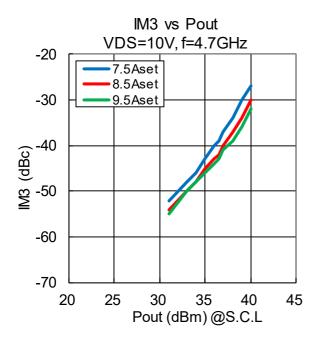
#### ·IM3 vs. Pout

VDS= 10 V, IDSset= 9.5 A, f= 4.4, 4.7, 5.0 GHz,  $\Delta$ f= 5 MHz , Ta= +25  $^{\circ}$ C



#### ·IM3 vs. Pout vs. IDSset

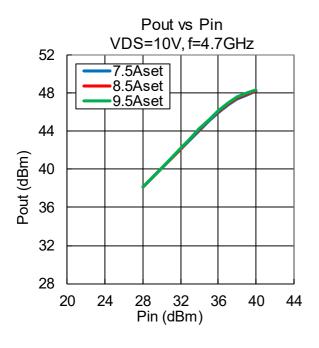
VDS= 10 V, f= 4.7 GHz, IDSset= 7.5A, 8.5A, 9.5A,  $\Delta$ f= 5 MHz , Ta= +25  $^{\circ}$ C

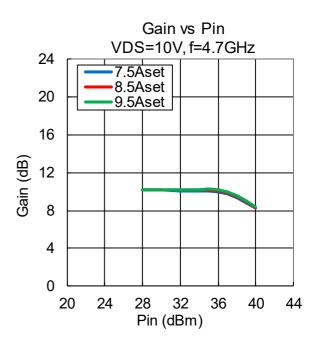


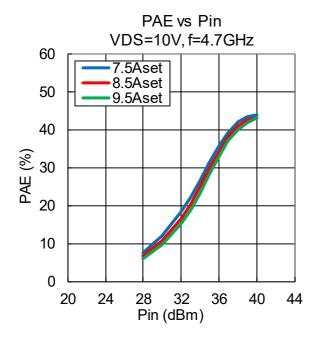


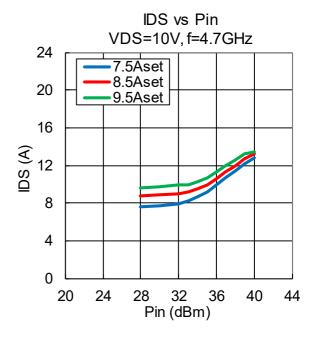
·Pout , Gain , PAE , IDS vs. Pin vs. IDSset

VDS= 10 V, IDSset= 7.5, 8.5, 9.5 A, f= 6.15 GHz, Ta= +25 °C





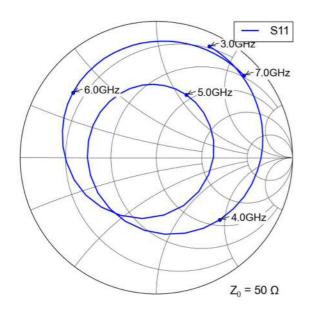


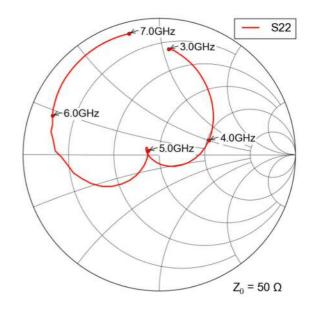


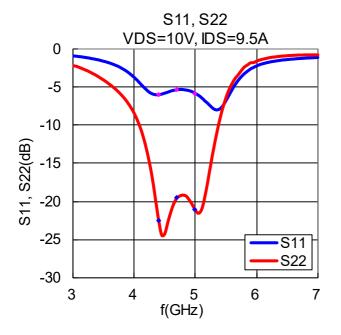


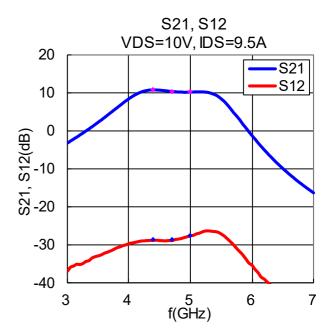
#### ·S-Parameters

VDS= 10 V, IDSset= 9.5 A, f= 3.0 to 7.0 GHz, Ta= +25  $^{\circ}$ C











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